

CSE 4217

CMOS LOGIC

# CMOS INTRODUCTION

- Complementary metal-oxide-semiconductor (CMOS) is a technology for constructing integrated circuits.
- In 1963, while working for Fairchild Semiconductor, Frank Wanlass patented CMOS (US patent 3,356,858).
- Use:
  - CMOS technology is used in microprocessors, microcontrollers, static RAM, and other digital logic circuits.
  - CMOS technology is also used for several analog circuits such as image sensors (CMOS sensor), data converters, and highly integrated transceivers for many types of communication.

# CMOS INTRODUCTION

- CMOS is also sometimes referred to as **Complementary-Symmetry Metal-Oxide-Semiconductor (or COS-MOS)**.
- The words "**complementary-symmetry**" refer to the fact that the typical design style with CMOS uses **complementary and symmetrical pairs of p-type and n-type** metal oxide semiconductor field effect transistors (MOSFETs) for logic functions.
- When a circuit contains both NMOS and PMOS transistors we say it is implemented in CMOS (Complementary MOS).

# CMOS CHARACTERISTICS

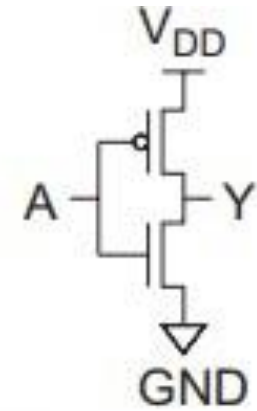
- Two important characteristics of CMOS devices are:
  - High noise immunity
  - Low static power consumption
- Since one transistor of the pair is always off, the series combination draws significant power only momentarily during switching between on and off states.
- Consequently, CMOS devices do not produce as much waste heat as other forms of logic, for example transistor-transistor logic (TTL) or NMOS logic, which normally have some standing current even when not changing state.
- CMOS also allows a high density of logic functions on a chip.
  - It was primarily for this reason that CMOS became the most used technology to be implemented in VLSI chips.

# CMOS LOGIC

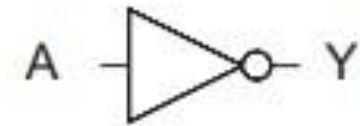
- Logic gates designed by CMOS devices:
  - Inverter
  - NAND
  - NOR
  - Compound Gates

# THE INVERTER

- CMOS inverter or NOT gate using one nMOS transistor and one pMOS transistor.
- The bar at the top indicates  $V_{DD}$  and the triangle at the bottom indicates GND.
- 



(a)



(b)

**TABLE 1.1** Inverter truth table

A	Y
0	1
1	0

**FIGURE 1.11**

Inverter schematic

(a) and symbol

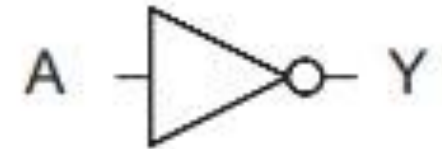
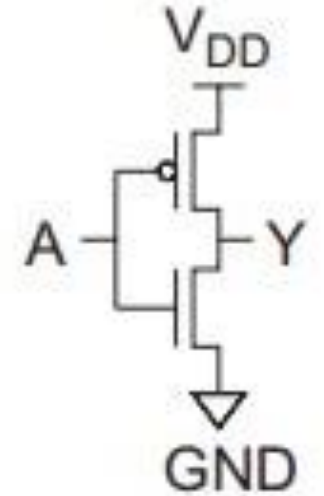
(b)  $Y = \bar{A}$

# THE INVERTER

- When the input **A** is **0**, the **nMOS** transistor is **OFF** and the **pMOS** transistor is **ON**. Thus, the output **Y** is **pulled up to 1** because it is connected to  $V_{DD}$  but not to GND.
- Conversely, when **A** is **1**, the **nMOS** is **ON**, the **pMOS** is **OFF**, and **Y** is **pulled down to 0**.

**TABLE 1.1** Inverter truth table

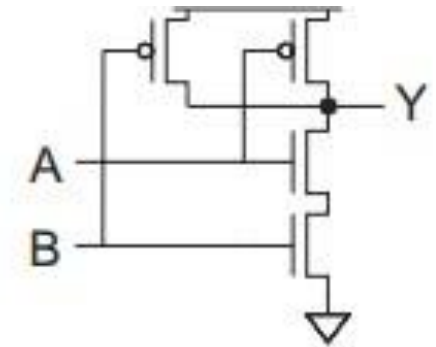
A	Y
0	1
1	0



**FIGURE 1.11**  
Inverter schematic  
(a) and symbol  
(b)  $Y = \bar{A}$

# NAND GATE

- It consists of two series nMOS transistors between Y and GND and two parallel pMOS transistors between Y and VDD.
- If either input A or B is 0, at least one of the nMOS transistors will be OFF, breaking the path from Y to GND.



(a)



(b)

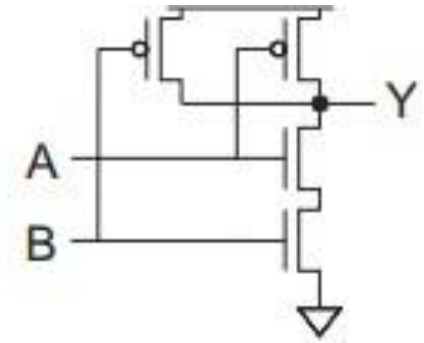
TABLE 1.2 NAND gate truth table

A	B	Pull-Down Network	Pull-Up Network	Y
0	0	OFF	ON	1
0	1	OFF	ON	1
1	0	OFF	ON	1
1	1	ON	OFF	0

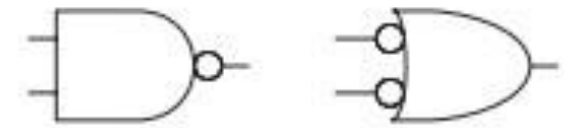
FIGURE 1.12 2-input NAND gate schematic (a) and symbol (b)  $Y = \overline{A \cdot B}$

# NAND GATE

- But at least one of the pMOS transistors will be ON, creating a path from Y to  $V_{DD}$ . Hence, the output Y will be 1.
- If both inputs are 1, both of the nMOS transistors will be ON and both of the pMOS transistors will be OFF. Hence, the output will be 0.



(a)



(b)

**FIGURE 1.12** 2-input NAND gate schematic (a) and symbol (b)  $Y = \overline{A \cdot B}$

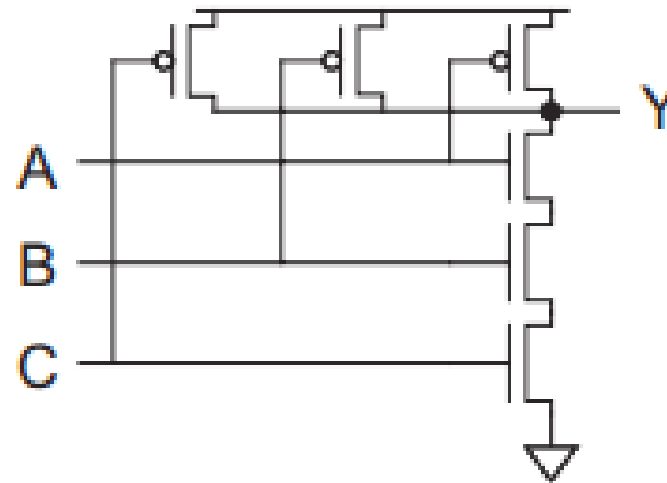
**TABLE 1.2** NAND gate truth table

A	B	Pull-Down Network	Pull-Up Network	Y
0	0	OFF	ON	1
0	1	OFF	ON	1
1	0	OFF	ON	1
1	1	ON	OFF	0

# NAND GATE

- 3-input NAND Gate
  - When any of the inputs are 0, the output is pulled high through the parallel pMOS transistors.
  - When all of the inputs are 1, the output is pulled low through the series nMOS t

- Draw truth table!!
- What about k-input NAND gate?



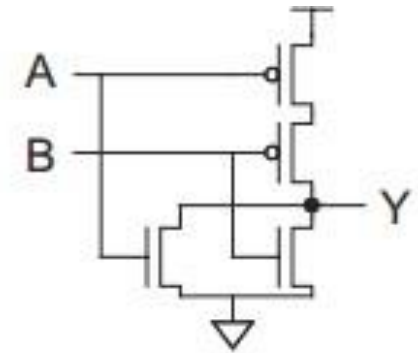
**FIGURE 1.13** 3-input NAND gate schematic  $Y = \overline{A \cdot B \cdot C}$

# NOR GATE

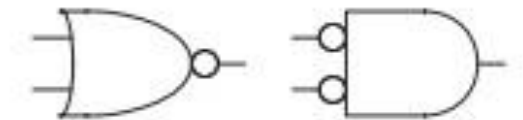
- The nMOS transistors are in parallel to pull the output low when either input is high.
- The pMOS transistors are in series to pull the output high when both inputs are low.

**TABLE 1.4** NOR gate truth table

<i>A</i>	<i>B</i>	<i>Y</i>
0	0	1
0	1	0
1	0	0
1	1	0



(a)



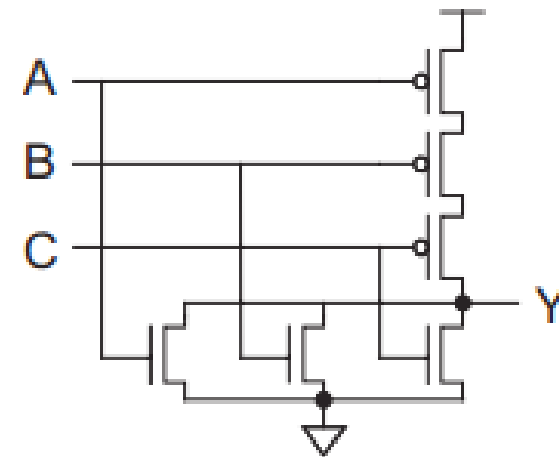
(b)

**FIGURE 1.16** 2-input NOR gate schematic (a) and symbol (b)  $Y = \overline{A + B}$

# NOR GATE

- 3-input NOR Gate
  - If any input is high, the output is pulled low through the parallel nMOS transistors.
  - If all inputs are low, the output is pulled high through the series pMOS transistors.

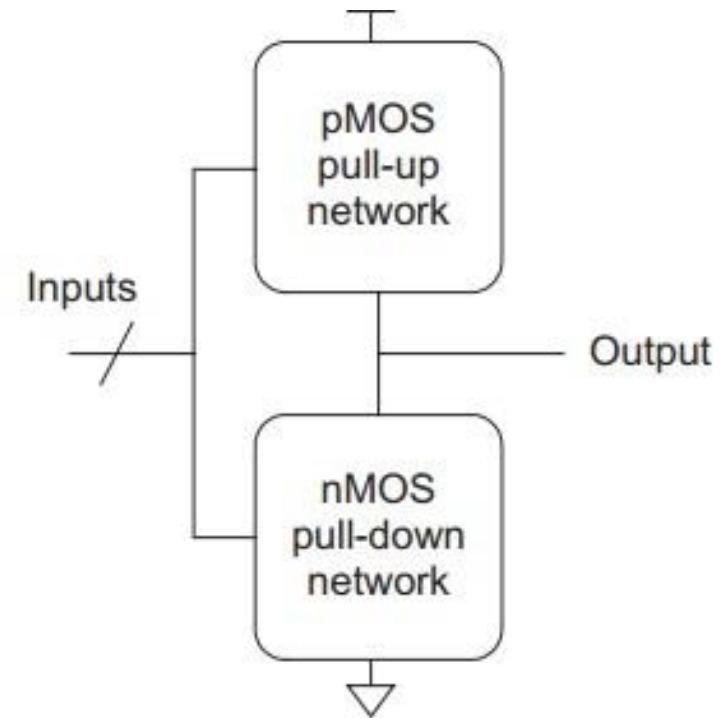
- Draw truth table!
- What about k-input NOR gate?



**FIGURE 1.17** 3-input NOR gate schematic  $Y = \overline{A + B + C}$

# CMOS LOGIC GATES

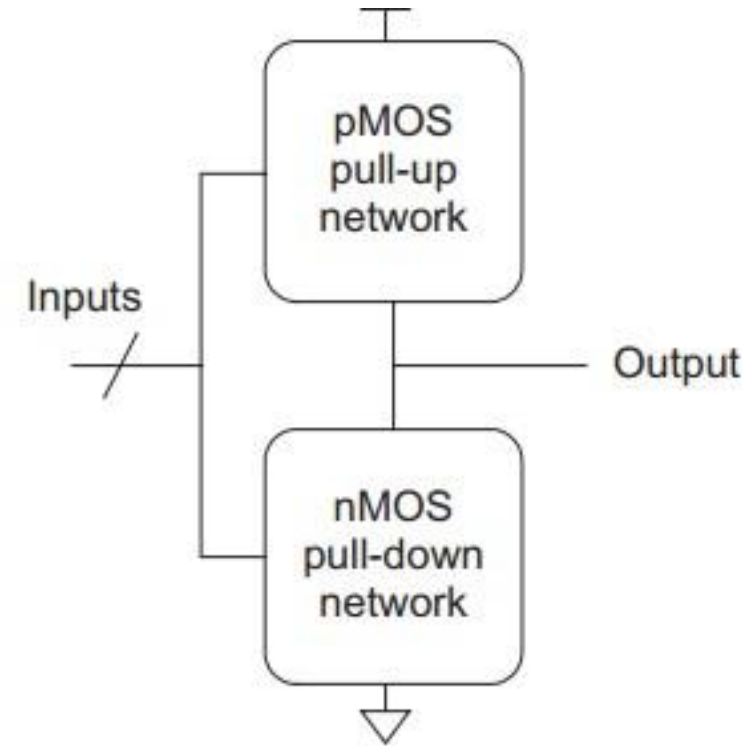
- The gates shown are examples of **static CMOS** logic gates, also called complementary CMOS gates.
- In general, a static CMOS gate has an **nMOS pull-down network** to connect the output to 0 (GND) and **pMOS pull-up network** to connect the output to 1 ( $V_{DD}$ ).
  - shown in Figure 1.14.
- 



**FIGURE 1.14** General logic gate using pull-up and pull-down networks

# CMOS LOGIC GATES

- The networks are arranged such that **one is ON and the other OFF** for any input pattern.
- The pull-up and pull-down networks in the inverter each consist of a single transistor.
- The NAND gate uses a series pull-down network and a parallel pullup network. More elaborate networks are used for more complex gates.



**FIGURE 1.14** General logic gate using pull-up and pull-down networks

# CMOS LOGIC GATES

- Two or more transistors in parallel are ON if any of the parallel transistors are ON.
- This is illustrated in Figure 1.15 for nMOS and pMOS transistor pairs.
- By using combinations of these constructions, CMOS combinational gates can be constructed.

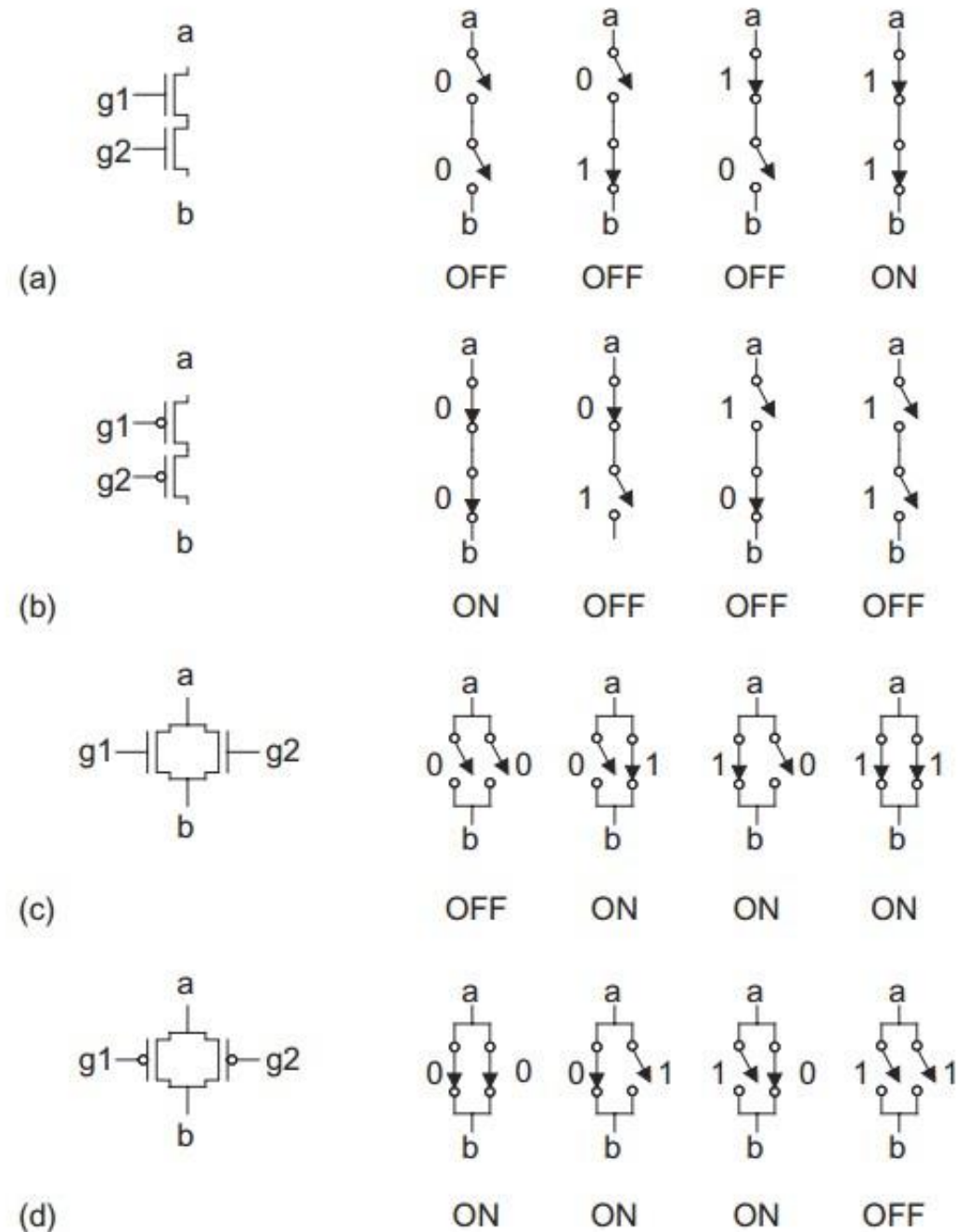


FIGURE 1.15 Connection and behavior of series and parallel transistors

# CMOS LOGIC GATES

- In general, when we join a pull-up network to a pull-down network to form a logic gate as shown in Figure 1.14, they **both will attempt to exert a logic level at the output**. The possible levels at the output are shown in Table 1.3.
- From this table it can be seen that the **output of a CMOS logic gate can be in four states**.
- The 1 and 0 levels have been encountered with the inverter and NAND gates, where either the pull-up or pull-down is OFF and the other structure is ON.

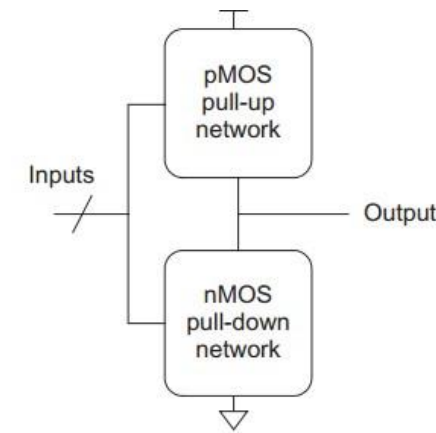


FIGURE 1.14 General logic gate using pull-up and pull-down networks

TABLE 1.3 Output states of CMOS logic gates

	pull-up OFF	pull-up ON
pull-down OFF	Z	1
pull-down ON	0	crowbarred (X)

# CMOS LOGIC GATES

- When both pull-up and pull-down are OFF, the high impedance or floating Z output state results.
  - This is of importance in multiplexers, memory elements, and tristate bus drivers.
- The crowbarred (or contention) X level exists when both pull-up and pull-down are simultaneously turned ON. Contention between the two networks results in an indeterminate output level and dissipates static power.
  - It is usually an “unwanted condition”.

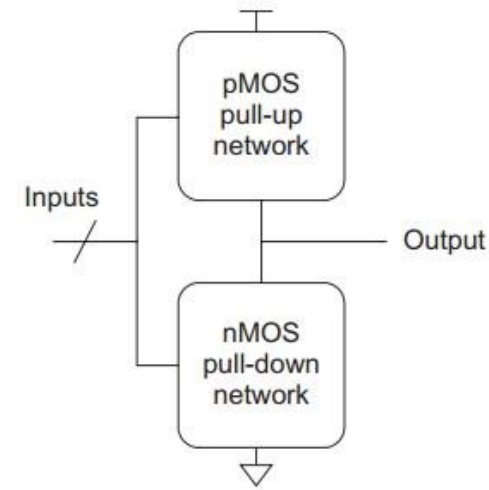


FIGURE 1.14 General logic gate using pull-up and pull-down networks

TABLE 1.3 Output states of CMOS logic gates

	pull-up OFF	pull-up ON
pull-down OFF	Z	1
pull-down ON	0	crowbarred (X)

# COMPOUND GATES

- A compound gate performing a more complex logic function in a single stage of logic is formed by using a **combination of series and parallel switch structures**.
- Example:
  - Sketch a static CMOS gate computing
  - $Y = \overline{(A \cdot B)} + (C \cdot D)$

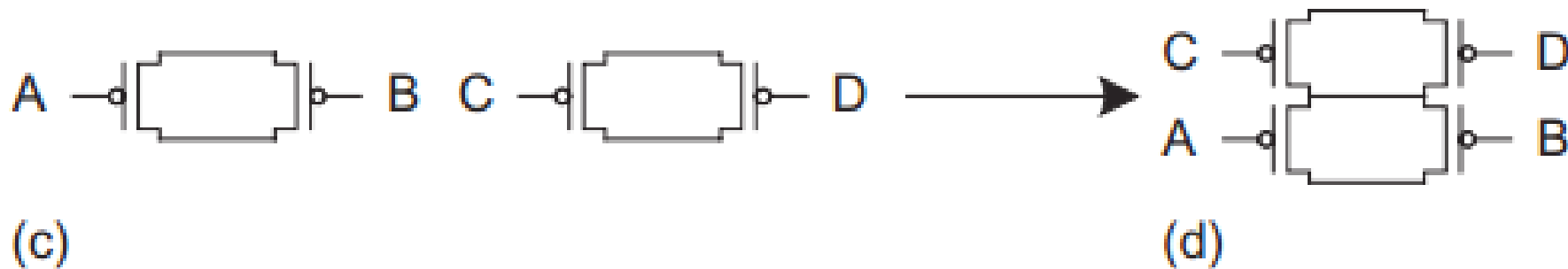
# COMPOUND GATES

- For the nMOS pull-down network, take the un-inverted expression  $((A \cdot B) + (C \cdot D))$  indicating when the output should be pulled to 0.
- The AND expressions  $(A \cdot B)$  and  $(C \cdot D)$  may be implemented by series connections of switches, as shown in Figure 1.18(a).
- Now ORing the result requires the parallel connection of these two structures, which is shown in Figure 1.18(b).



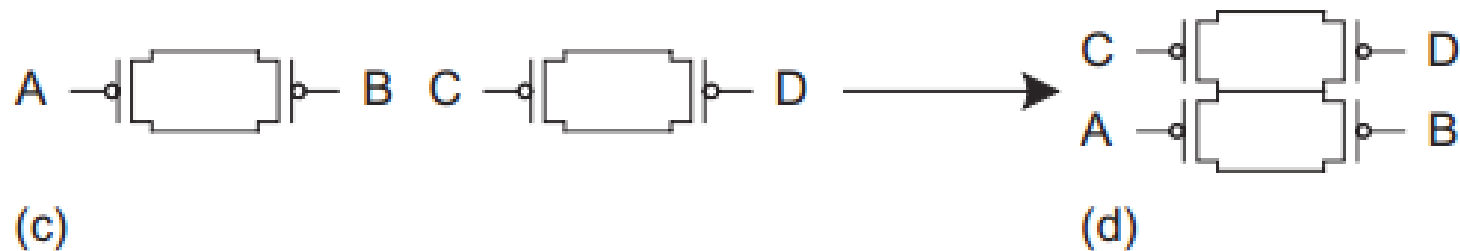
# COMPOUND GATES

- For the pMOS pull-up network, we must compute the complementary expression using switches that turn on with inverted polarity.
- By De Morgan's Law, this is equivalent to interchanging AND and OR operations.



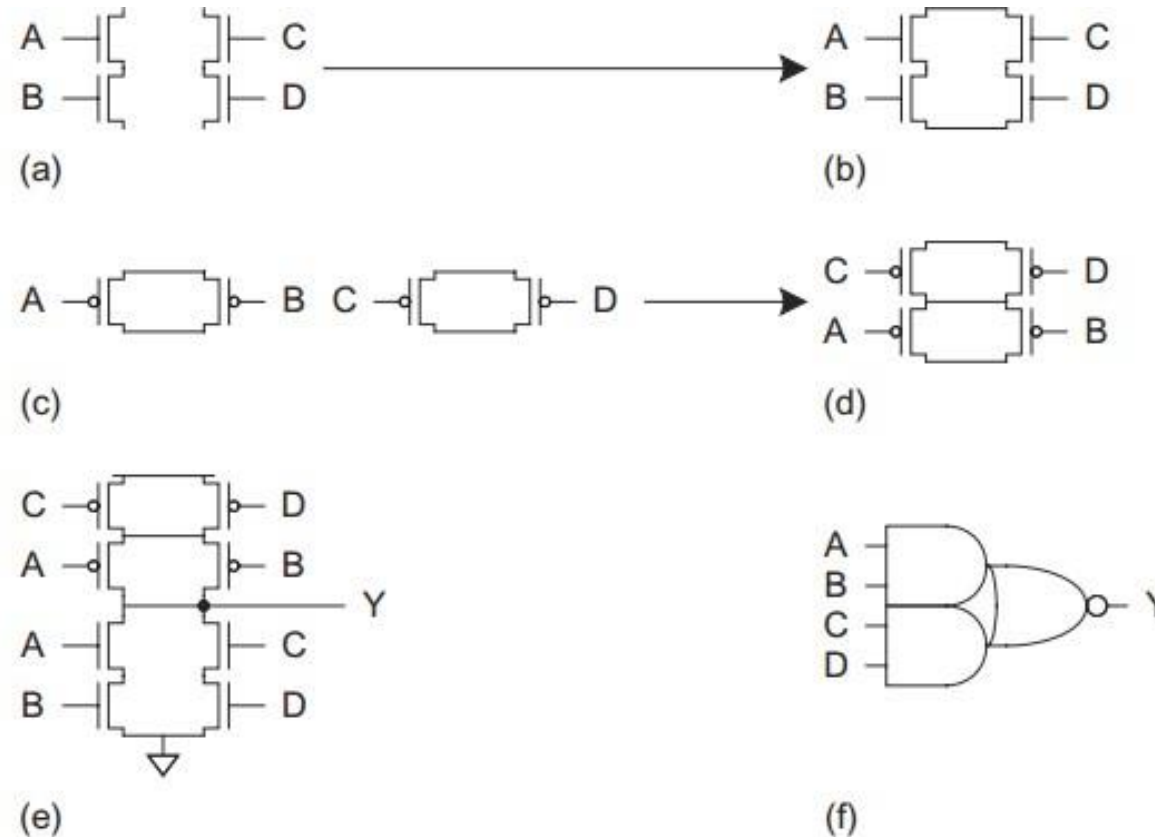
# COMPOUND GATES

- Hence, transistors that appear in series in the pull-down network must appear in parallel in the pull-up network.
- Transistors that appear in parallel in the pulldown network must appear in series in the pull-up network.
- This principle is called “Conduction Complements” and has already been used in the design of the NAND and NOR gates.
- In the pull-up network, the parallel combination of A and B is placed in series with the parallel combination of C and D. This progression is evident in Figure 1.18(c) and Figure 1.18(d).



# COMPOUND GATES

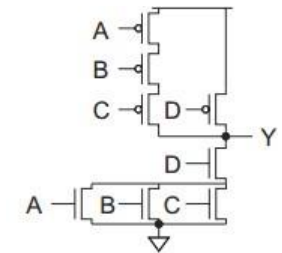
- Putting the networks together yields the full schematic (Figure 1.18(e)). The symbol is shown in Figure 1.18(f).



**FIGURE 1.18** CMOS compound gate for function  $Y = (A \cdot B) + (C \cdot D)$

# COMPOUND GATES

- Example
- Sketch a static CMOS gate computing
- 
- $Y = \overline{(A + B + C)} \cdot D$
- 
- The nMOS pull-down network pulls the output low if D is 1 and either A or B or C are 1.
- So D is in series with the parallel combination of A, B, and C.
- The pMOS pull-up network is the conduction complement.
- So D must be in parallel with the series combination of A, B, and C.



**FIGURE 1.19**  
CMOS compound gate  
for function  
 $Y = \overline{(A + B + C)} \cdot D$

# REFERENCE

- Slide
- Weste
  - 1.4.1
  - 1.4.2
  - 1.4.3
  - 1.4.4
  - 1.4.5

# CMOS Logic



# PASS TRANSISTORS

- The **strength** of a signal is measured by how **closely it approximates an ideal voltage source**.
- In general, the stronger a signal, the more current it can **source or sink**. The power supplies, or rails, ( $V_{DD}$  and GND) are the source of the strongest 1s and 0s.

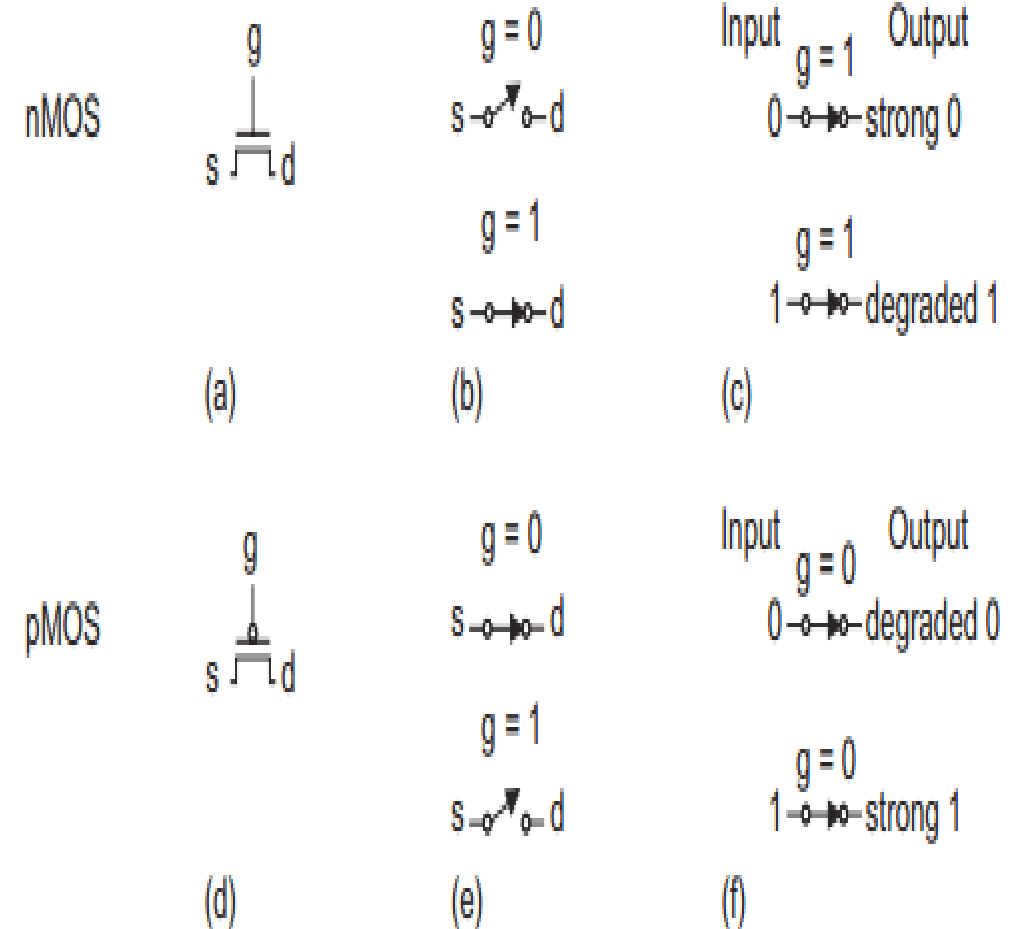


FIGURE 1.20 Pass transistor strong and degraded outputs

# PASS TRANSISTORS

- An **nMOS** transistor is an **almost perfect switch** when **passing a 0** and thus we say it passes a **strong 0**. However, the nMOS transistor is **imperfect at passing a 1**. The high voltage level is **somewhat less than VDD**.
  - We say it passes a **degraded or weak 1**.
- A pMOS transistor again has the opposite behavior, passing **strong 1s but degraded 0s**.
- When an **nMOS or pMOS is used alone as an imperfect switch**, we sometimes call it a **pass transistor**.

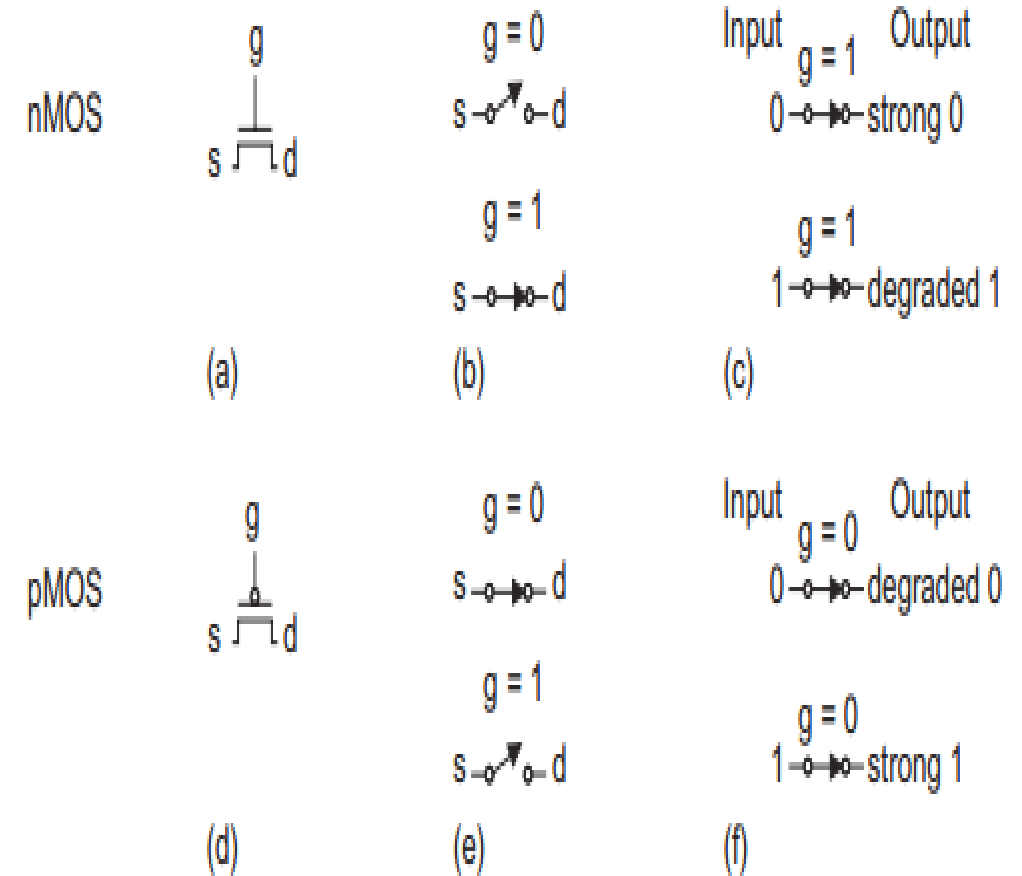


FIGURE 1.20 Pass transistor strong and degraded outputs

# TRANSMISSION GATES

- By combining an **nMOS** and a **pMOS** transistor in parallel (Figure 1.21(a)), we obtain a **switch** that turns on when a 1 is applied to  $g$  (Figure 1.21(b)) in which 0s and 1s are both passed in an acceptable fashion (Figure 1.21(c)).
  - We term this a **transmission gate** or **pass gate**.

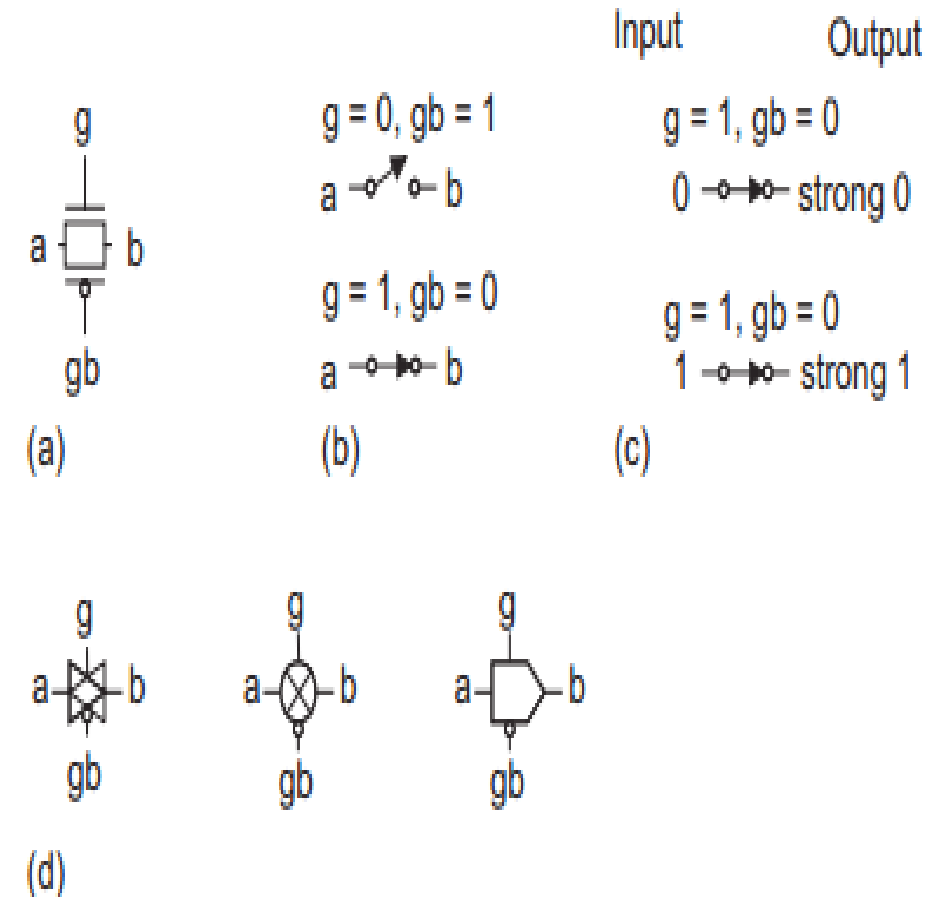


FIGURE 1.21 Transmission gate

# TRANSMISSION GATES

- Note that both the **control input and its complement are required** by the transmission gate.
  - This is called **double rail logic**.
- Some circuit symbols for the transmission gate are shown in Figure 1.21(d).

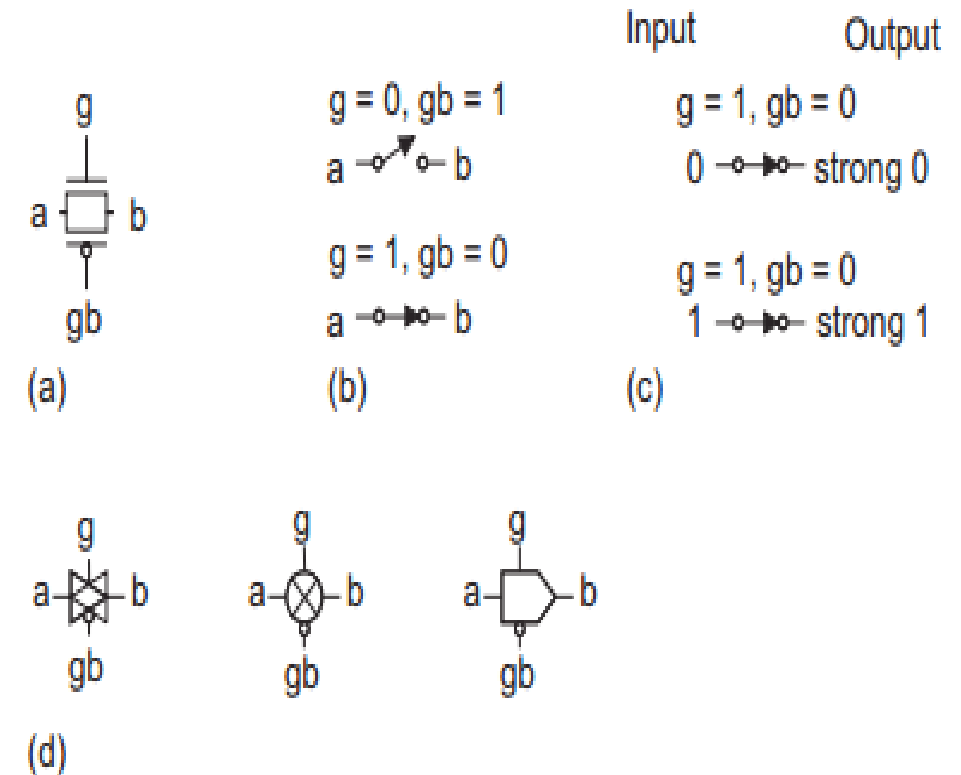
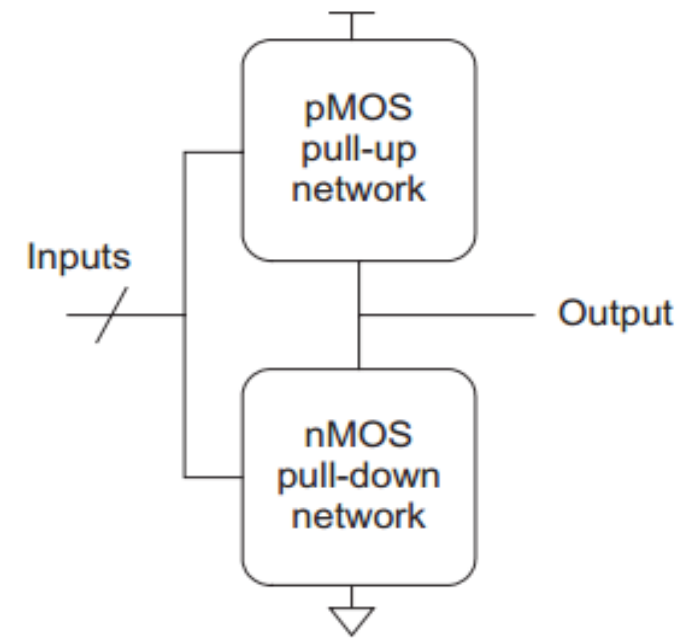


FIGURE 1.21 Transmission gate

# FULLY RESTORED LOGIC GATE

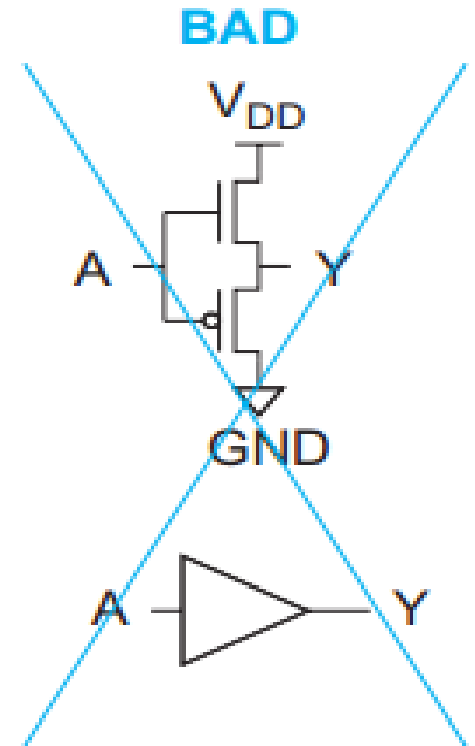
- In all of our examples so far, the inputs drive the gate terminals of nMOS transistors in the pull-down network and pMOS transistors in the complementary pull-up network.
- Thus, the **nMOS transistors only need to pass 0s** and the **pMOS only pass 1s**, so the output is always strongly driven and the levels are never degraded.
  - This is called a **fully restored logic gate** and simplifies circuit design considerably.



**FIGURE 1.14** General logic gate using pull-up and pull-down networks

# NON-INVERTING GATES

- A consequence of the design of static CMOS gates is that they must be **inverting**.
- The **nMOS pull-down network turns ON when inputs are 1, leading to 0 at the output.**
  - We might be tempted to turn the **transistors upside down to build a noninverting gate.**
- Unfortunately, now **both** the nMOS and pMOS transistors produce **degraded outputs**, so the technique **should be avoided**.



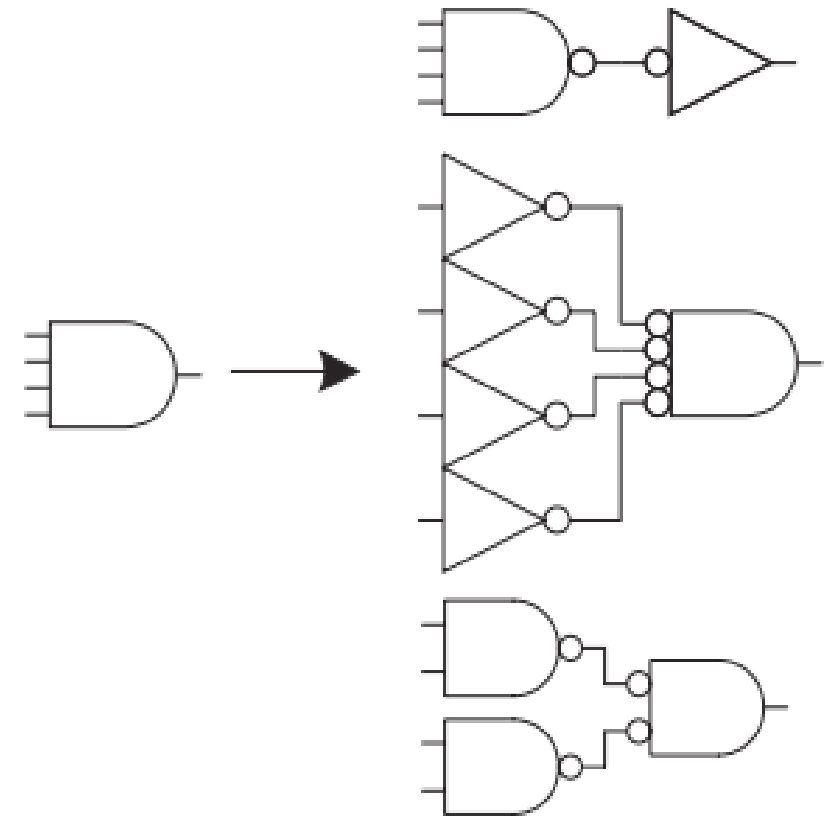
**FIGURE 1.22**  
Bad noninverting buffer

# NON-INVERTING GATES

Instead, we can build **non-inverting** functions from **multiple stages of inverting gates**.

- Figure 1.23 shows several ways to build a 4-input AND gate from **two levels of inverting static CMOS gates**.

Each design has different speed, size, and power trade-offs.



**FIGURE 1.23** Various implementations of a CMOS 4-input AND gate

# NON-INVERTING GATES

- Remember,  $Y = \overline{(A \cdot B) + (C \cdot D)}$  ?
- The compound gate of Figure 1.18 could be built with two AND gates, an OR gate, and an inverter.
- The AND and OR gates in turn could be constructed from **NAND/NOR** gates and inverters, as shown in Figure 1.24, using a **total of 20 transistors, as compared to eight** in Figure 1.18.
  - Good CMOS logic designers exploit the **efficiencies of compound gates rather than using large numbers of AND/OR gates.**

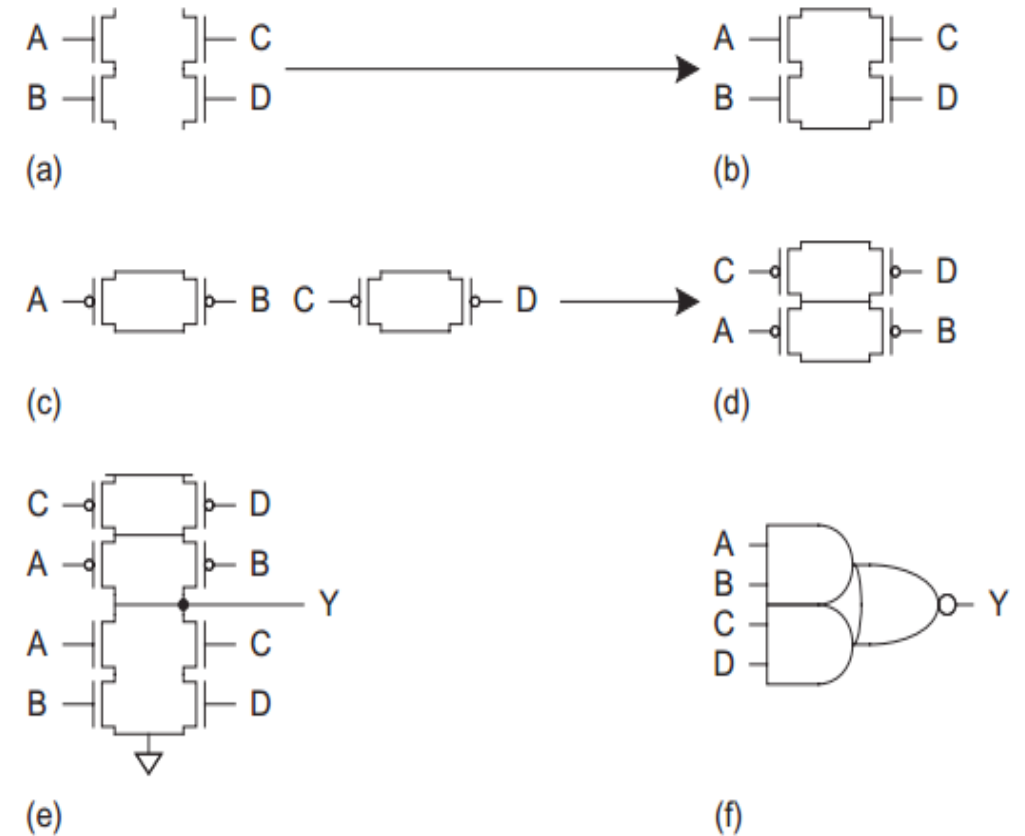


FIGURE 1.18 CMOS compound gate for function  $Y = \overline{(A \cdot B) + (C \cdot D)}$

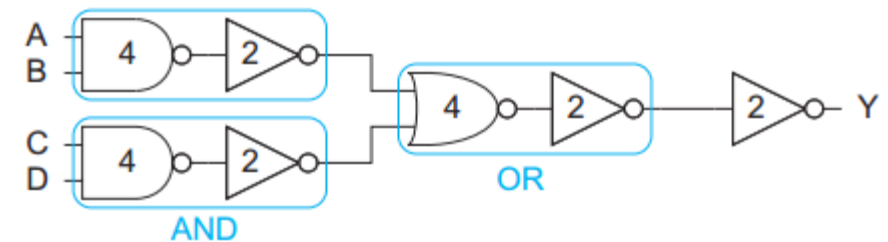
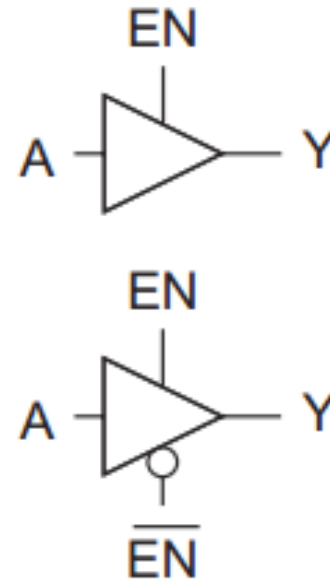


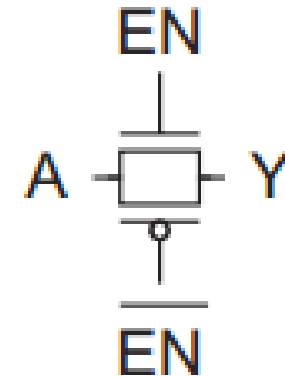
FIGURE 1.24 Inefficient discrete gate implementation of AOI22 with transistor counts indicated

# TRISTATES

- Figure 1.25 shows symbols for a **tristate buffer**.
- When the **enable input EN is 1**, the output Y equals the input A, just as in an **ordinary buffer**. When the **enable is 0**, Y is left **floating (a 'Z' value)**.
- The transmission gate in Figure 1.26 has the same truth table as a tristate buffer. It only requires two **transistors but it is a non-restoring circuit**.
  - If the input is noisy or otherwise degraded, the output will receive the same noise.



**FIGURE 1.25**  
Tristate buffer  
symbol



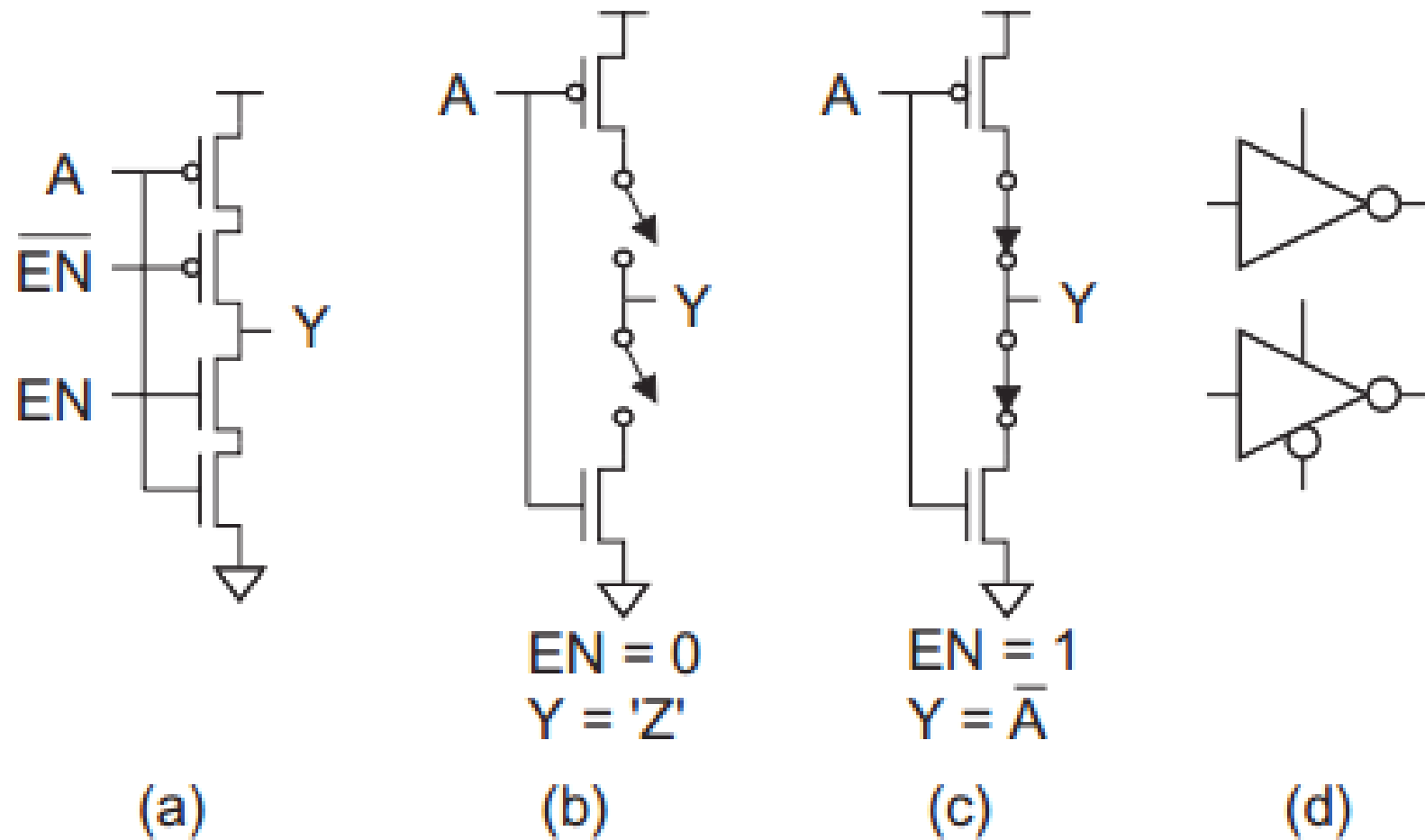
**FIGURE 1.26**  
Transmission gate

**TABLE 1.5** Truth table for tristate

EN / $\overline{\text{EN}}$	A	Y
0 / 1	0	Z
0 / 1	1	Z
1 / 0	0	0
1 / 0	1	1

# TRISTATE INVERTER

- Figure 1.27(a) shows **a tristate inverter**.
- The output is actively driven from  $V_{DD}$  or GND
  - so it is a **restoring logic gate**.
- Unlike any of the gates considered so far, **the tristate inverter does not obey the conduction complements rule**.
  - Because it **allows the output to float under certain input combinations**.
  - When **EN is 0** (Figure 1.27(b)), **both enable transistors are OFF, leaving the output floating**.
  - When **EN is 1** (Figure 1.27(c)), **both enable transistors are ON**. They are **conceptually removed** from the circuit, leaving a simple inverter.
- Figure 1.27(d) shows symbols for the tristate inverter. The complementary enable signal can be generated internally or can be routed to the cell explicitly.
- A tristate buffer can be built as an ordinary inverter followed by a tristate inverter.



**FIGURE 1.27** Tristate Inverter



# MULTIPLEXERS

- Multiplexers are **key components** in CMOS memory elements and data manipulation structures.
- A multiplexer chooses the output from among **several inputs based on a select signal**.
  - A 2-input, or 2:1 multiplexer, chooses input D0 when the select is 0 and input D1 when the select is 1.
  - The truth table is given in Table 1.6
  - The logic function is  **$Y = S \cdot D0 + \bar{S} \cdot D1$** .

**TABLE 1.6** Multiplexer truth table

$S / \bar{S}$	$D1$	$D0$	$Y$
0 / 1	X	0	0
0 / 1	X	1	1
1 / 0	0	X	0
1 / 0	1	X	1

# REFERENCE

- Weste
  - 1.4.6
  - 1.4.7
  - 1.4.8